

Unipolar Hall Switch

High Precision Hall Effect Switch for Consumer Applications

TLV4964-4TA

TLV4964-4TB

SP001274780

SP001283600

TLV4964-4T

Data Sheet

Revision 1.2, 2019-12-20

Sense & Control

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Product description

1 Product description



1.1 Overview

| Characteristic | Supply Voltage | Supply Current | Sensitivity | Interface | Temperature |
|-----------------------------|----------------|----------------|---------------------------------------|-------------------|----------------|
| Unipolar Hall Effect Switch | 3.0 V ~ 26 V | 1.6 mA | B_{OP} : 10 mT B_{RP} : 8.5 mT | Open Drain Output | -40°C to 125°C |

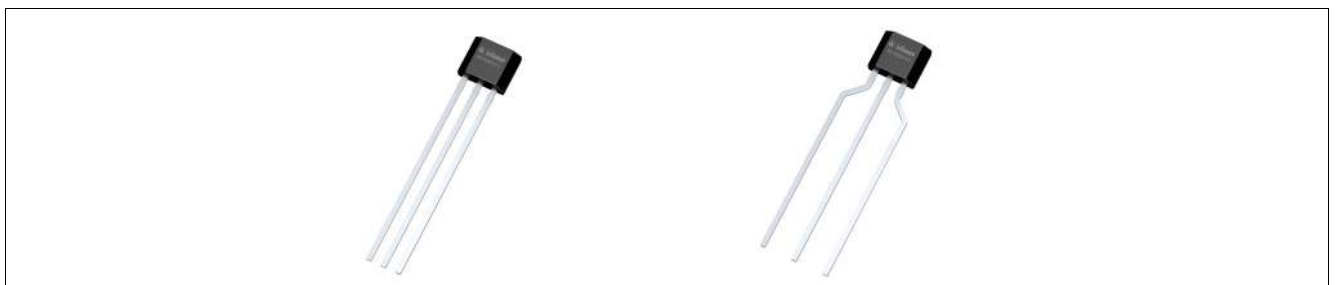


Figure 1 TLV4964-4T in the TO92S-3-1 and TO92S-3-2 package

1.2 Features

- 3.0 V to 26 V operating supply voltage
- Operation from unregulated power supply
- Output overcurrent and overtemperature protection
- Active error compensation
- High stability of magnetic thresholds
- High ESD performance
- Leaded, halogen-free package TO92S-3-1 for TLV4964-4TA, TO92S-3-2 for TLV4964-4TB

For automotive applications please refer to the Infineon TLE Hall Switches/Latches series.

Table 1 Ordering information

| Product name | Product type | Ordering code | Package |
|--------------|----------------------|---------------|-----------------------|
| TLV4964-4TA | Unipolar Hall Switch | SP001274780 | TO92S-3-1 (Bulk) |
| TLV4964-4TB | Unipolar Hall Switch | SP001283600 | TO92S-3-2 (Ammo pack) |

1) Only the package is halogen-free.

Product description**1.3 Target applications**

Target applications for the TLV496x Hall Switch family are all applications which require a high precision Hall Switch with an operating temperature range from -40°C to 125°C.

The TLV4964-4T is a unipolar switch with a typical operating point $B_{OP} = 10 \text{ mT}$ and a hysteresis of $B_{HYS} = 1.5 \text{ mT}$. It is ideally suited for various position detection applications.

Functional description

2 Functional description

2.1 General

The TLV4964-4T is an integrated Hall effect designed specifically for highly accurate applications with superior supply voltage capability and temperature stability of the magnetic thresholds.

2.2 Pin configuration (top view)

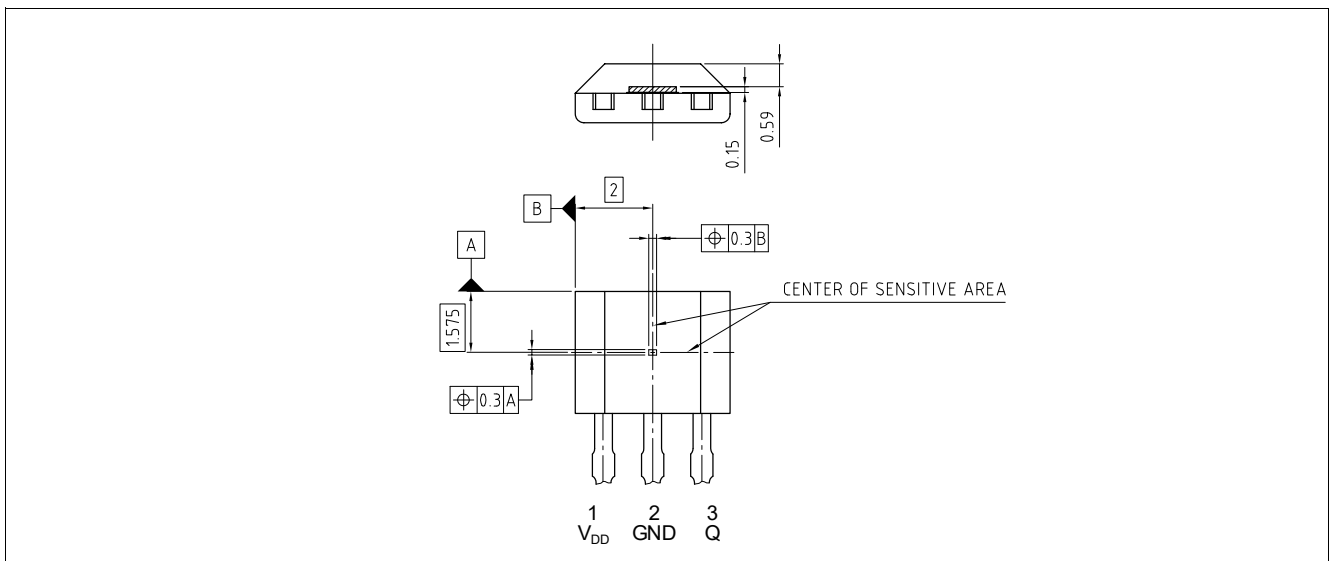


Figure 2 Pin configuration and center of sensitive area

2.3 Pin description

Table 2 Pin description

| Pin no. | Symbol | Function |
|---------|--------|----------------|
| 1 | VDD | Supply voltage |
| 2 | GND | Ground |
| 3 | Q | Output |

Functional description

2.4 Block diagram

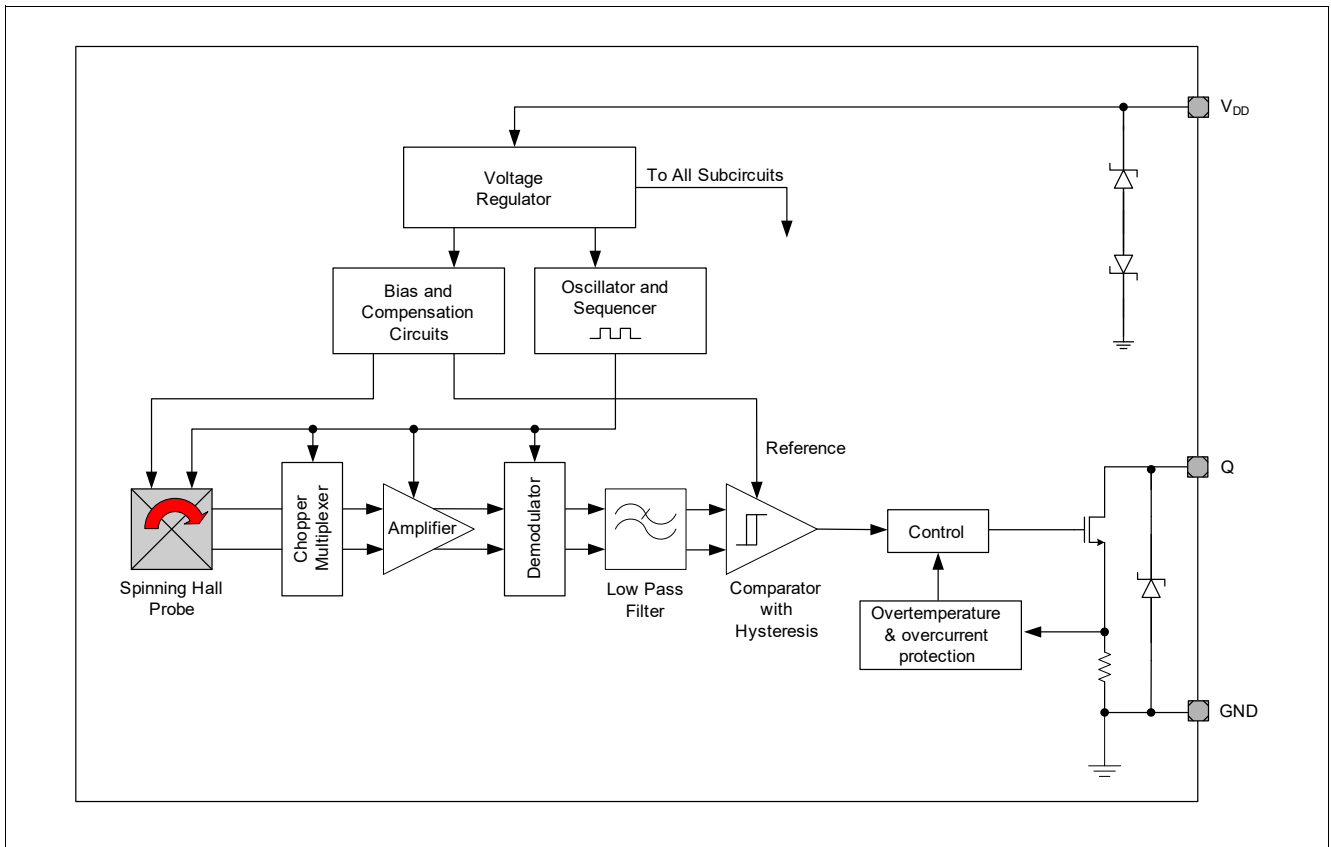


Figure 3 Functional block diagram TLV4964-4T

Functional description

2.5 Functional block description

The chopped Hall IC switch comprises a Hall probe, bias generator, compensation circuits, oscillator and output transistor.

The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce influence of technology variations.

The active error compensation (chopping technique) rejects offsets in the signal path and the influence of mechanical stress to the Hall probe caused by molding and soldering processes and other thermal stress in the package. The chopped measurement principle together with the threshold generator and the comparator ensures highly accurate and temperature stable magnetic thresholds.

The output transistor has an integrated overcurrent and overtemperature protection.

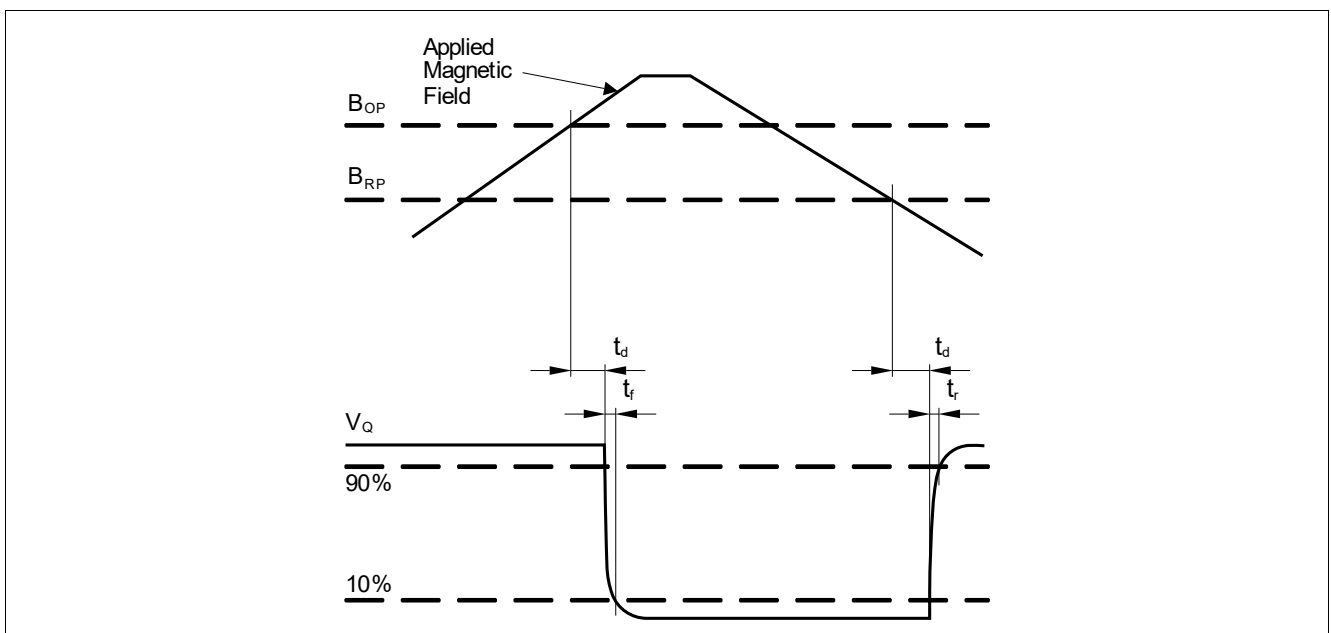


Figure 4 Timing diagram TLV4964-4T

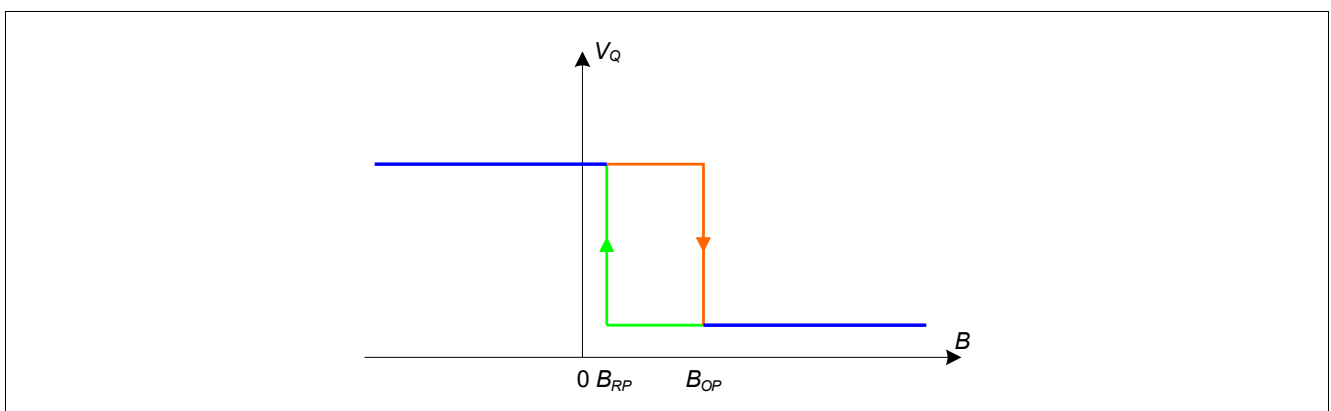


Figure 5 Output signal TLV4964-4T

Functional description

2.6 Default start-up behavior

The magnetic thresholds exhibit a hysteresis $B_{HYS} = B_{OP} - B_{RP}$. In case of a power-on with a magnetic field B within hysteresis ($B_{OP} > B > B_{RP}$) the output of the sensor is set to the pull up voltage level (V_Q) per default. After the first crossing of B_{OP} or B_{RP} of the magnetic field the internal decision logic is set to the corresponding magnetic input value.

V_{DDA} is the internal supply voltage which is following the external supply voltage V_{DD} .

This means for $B > B_{OP}$ the output is switching, for $B < B_{RP}$ and $B_{OP} > B > B_{RP}$ the output stays at V_Q .

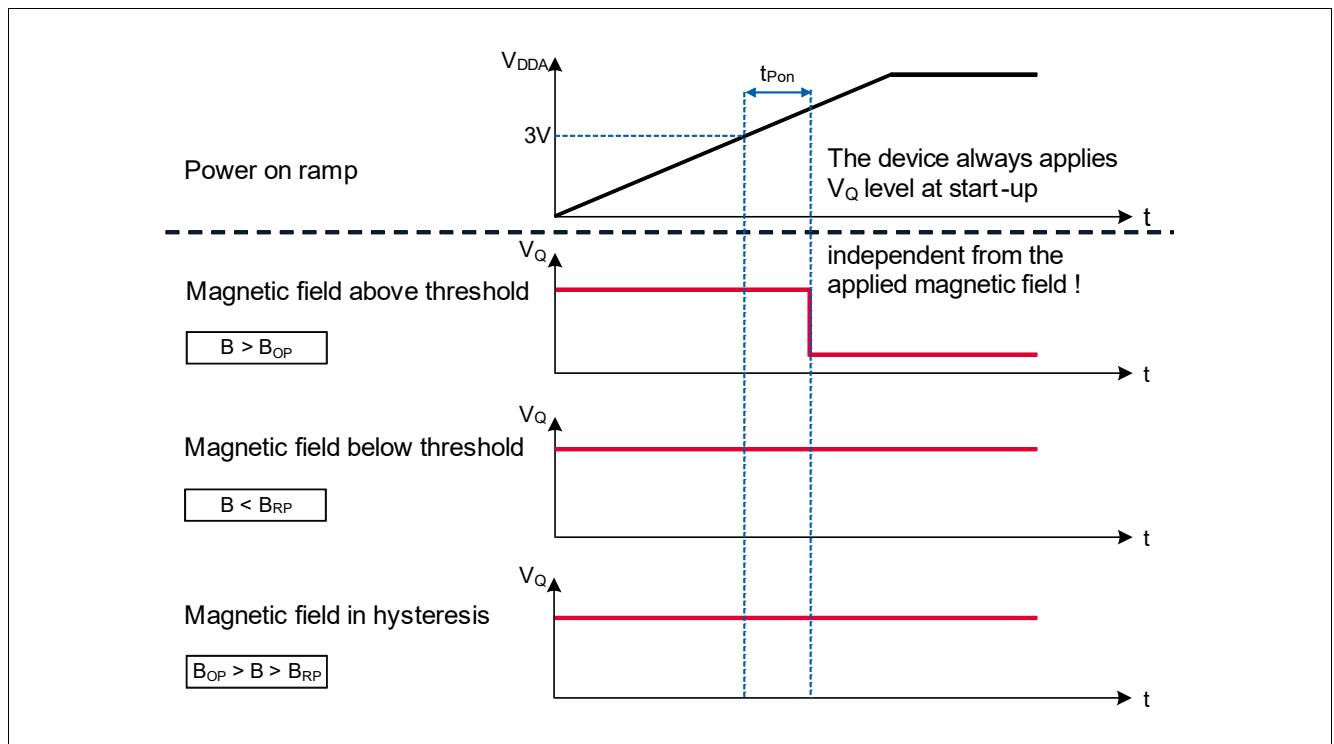


Figure 6 Start-up behavior of the TLV4964-4T

Specification

3 Specification

3.1 Application circuit

The following **Figure 7** shows the basic option of an application circuit. Only a pull-up resistor R_Q is necessary. The resistor R_Q has to be in a dimension to match the applied V_S to keep I_Q limited to the operating range of maximum 25 mA.

e.g.: $V_S = 12\text{ V}$; $I_Q = 12\text{ V}/1200\ \Omega = 10\text{ mA}$

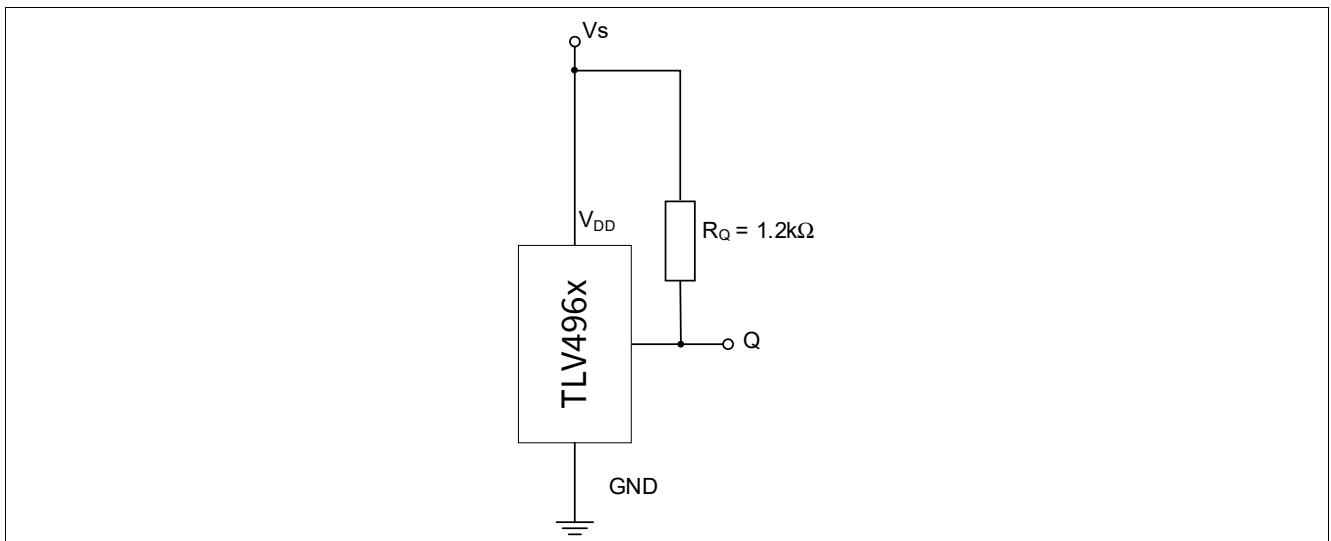


Figure 7 Basic application circuit #1: only pull-up resistor is necessary

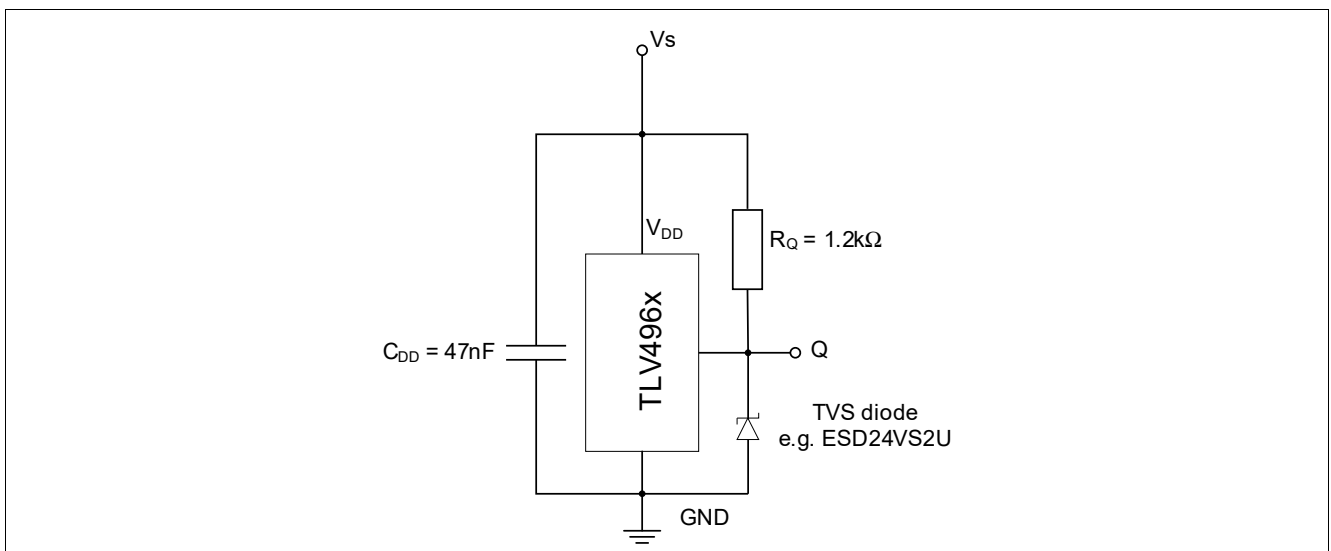


Figure 8 Enhanced application circuit #2: for extended ESD robustness

With an additional capacitor C_{DD} and a transient voltage suppression (TVS) diode an extended ESD robustness on system level is achieved (**Figure 8**).

Specification

3.2 Absolute maximum ratings

Table 3 Absolute maximum rating parameters

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|--|------------|--------|------|------|------|---------------------------------|
| | | Min. | Typ. | Max. | | |
| Supply voltage ¹⁾ | V_{DD} | 3 | – | 26 | V | – |
| Output voltage | V_Q | -0.5 | – | 26 | V | – |
| Reverse output current | I_Q | -70 | – | – | mA | – |
| Junction temperature ¹⁾ | T_J | -40 | – | 150 | °C | – |
| Storage temperature | T_S | -40 | – | 150 | °C | – |
| Thermal resistance Junction ambient | R_{thJA} | – | – | 250 | K/W | for TO92S-3-1, TO92S-3-2 (2s2p) |

1) This lifetime statement is an anticipation based on an extrapolation of Infineon's qualification test results. The actual lifetime of a component depends on its form of application and type of use etc. and may deviate from such statement. The lifetime statement shall in no event extend the agreed warranty period.

Attention: *Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.*

Calculation of the dissipated power P_{DIS} and junction temperature T_J of the chip (TO92S example):

e.g. for: $V_{DD} = 12\text{ V}$, $I_S = 2.5\text{ mA}$, $V_{QSAT} = 0.5\text{ V}$, $I_Q = 20\text{ mA}$

Power dissipation: $P_{DIS} = 12\text{ V} \times 2.5\text{ mA} + 0.5\text{ V} \times 20\text{ mA} = 30\text{ mW} + 10\text{ mW} = 40\text{ mW}$

Temperature $\Delta T = R_{thJA} \times P_{DIS} = 250\text{ K/W} \times 40\text{ mW} = 10\text{ K}$

For $T_A = 50^\circ\text{C}$: $T_J = T_A + \Delta T = 50^\circ\text{C} + 10\text{ K} = 60^\circ\text{C}$

Specification

Table 4 ESD protection¹⁾ ($T_A = 25^\circ\text{C}$)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|---------------------------------|------------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| ESD voltage (HBM) ²⁾ | V_{ESD} | -4 | – | 4 | kV | $R = 1.5 \text{ k}\Omega$, $C = 100 \text{ pF}$ |
| ESD voltage (CDM) ³⁾ | V_{ESD} | -1 | – | 1 | kV | – |

1) Characterization of ESD is carried out on a sample basis, not subject to production test.

2) Human Body Model (HBM) tests according to ANSI/ESDA/JEDEC JS-001.

3) Charge device model (CDM) tests according to JESD22-C101.

3.3 Operating range

The following operating conditions must not be exceeded in order to ensure correct operation of the TLV4964-4T.

All parameters specified in the following sections refer to these operating conditions unless otherwise mentioned.

The maximum tested magnetic field is 600 mT.

Table 5 Operating conditions parameters

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|-----------------------|-----------------|--------|------|------------------|------------------|--|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{DD} | 3.0 | – | 26 ¹⁾ | V | – |
| Output voltage | V_{Q} | 3.0 | – | 26 | V | – |
| Operation temperature | T_A | -40 | – | 125 | $^\circ\text{C}$ | $R_{\text{thJA}} \leq 250 \text{ K/W}$ |
| Output current | I_{Q} | 0 | – | 25 | mA | – |

1) Latch-up test with factor 1.5 is not covered. Please see max ratings also.

Specification

3.4 Electrical and magnetic characteristics

Product characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production and correspond to $V_{DD} = 12\text{ V}$ and $T_A = 25^\circ\text{C}$. The below listed specification is valid in combination with the application circuit shown in [Figure 7](#) and [Figure 8](#).

Table 6 General electrical characteristics

| Parameter | Symbol | Values | | | Unit | Note or Test Condition |
|--------------------------------|--------------|--------|------|------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Supply current | I_S | 1.1 | 1.6 | 2.5 | mA | – |
| Output current limitation | I_{QLIMIT} | 30 | 56 | 70 | mA | internally limited and thermal shutdown |
| Output fall time ¹⁾ | t_f | 0.17 | 0.4 | 1 | μs | 1.2 k Ω / 50 pF, see Figure 4 |
| Output rise time ¹⁾ | t_r | 0.4 | 0.5 | 1 | μs | 1.2 k Ω / 50 pF, see Figure 4 |
| Delay time ¹⁾²⁾ | t_d | 12 | 15 | 30 | μs | see Figure 4 |
| Power-on time ¹⁾³⁾ | t_{PON} | – | 80 | 150 | μs | $V_{DD} = 3\text{ V}$, $B \leq B_{RP} - 0.5\text{ mT}$ or $B \geq B_{OP} + 0.5\text{ mT}$ |

- 1) Not subject to production test, verified by design/characterization.
- 2) Systematic delay between magnetic threshold reached and output switching.
- 3) Time from applying $V_{DD} = 3.0\text{ V}$ to the sensor until the output is valid.

Specification

Table 7 Magnetic characteristics

| Parameter | Symbol | T (°C) | Values | | | Unit | Note / Test Condition |
|---|-----------|--------|--------|-------|------|-------|-----------------------|
| | | | Min. | Typ. | Max. | | |
| Operating point | B_{OP} | -40 | 7.8 | 11.7 | 15.6 | mT | - |
| | | 25 | 6.5 | 10.0 | 13.5 | | |
| | | 125 | 4.6 | 7.4 | 10.3 | | |
| Release point | B_{RP} | -40 | 6.5 | 9.9 | 13.4 | mT | - |
| | | 25 | 5.4 | 8.5 | 11.6 | | |
| | | 125 | 3.7 | 6.3 | 8.9 | | |
| Hysteresis | B_{HYS} | -40 | 1.0 | 1.8 | 2.5 | mT | - |
| | | 25 | 0.8 | 1.5 | 2.2 | | |
| | | 125 | 0.5 | 1.1 | 1.7 | | |
| Temperature compensation of magnetic thresholds ¹⁾ | T_C | - | - | -2600 | - | ppm/K | - |

1) Not subject to production test, verified by design/characterization.

Field direction definition

Positive magnetic fields are defined with the south pole of the magnet to the branded side of package.

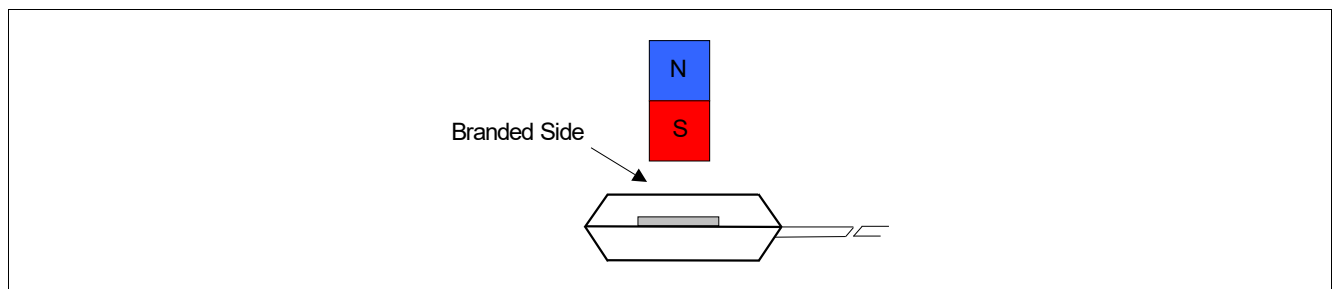


Figure 9 Definition of magnetic field direction T092S-3-1, T092S-3-2

Package information

4 Package information

The TLV4964-4TA is available in Bulk packing with TO92S-3-1-package.

The TLV4964-4TB is available in AMMO packing with TO92S-3-2-package.

4.1 Package outline

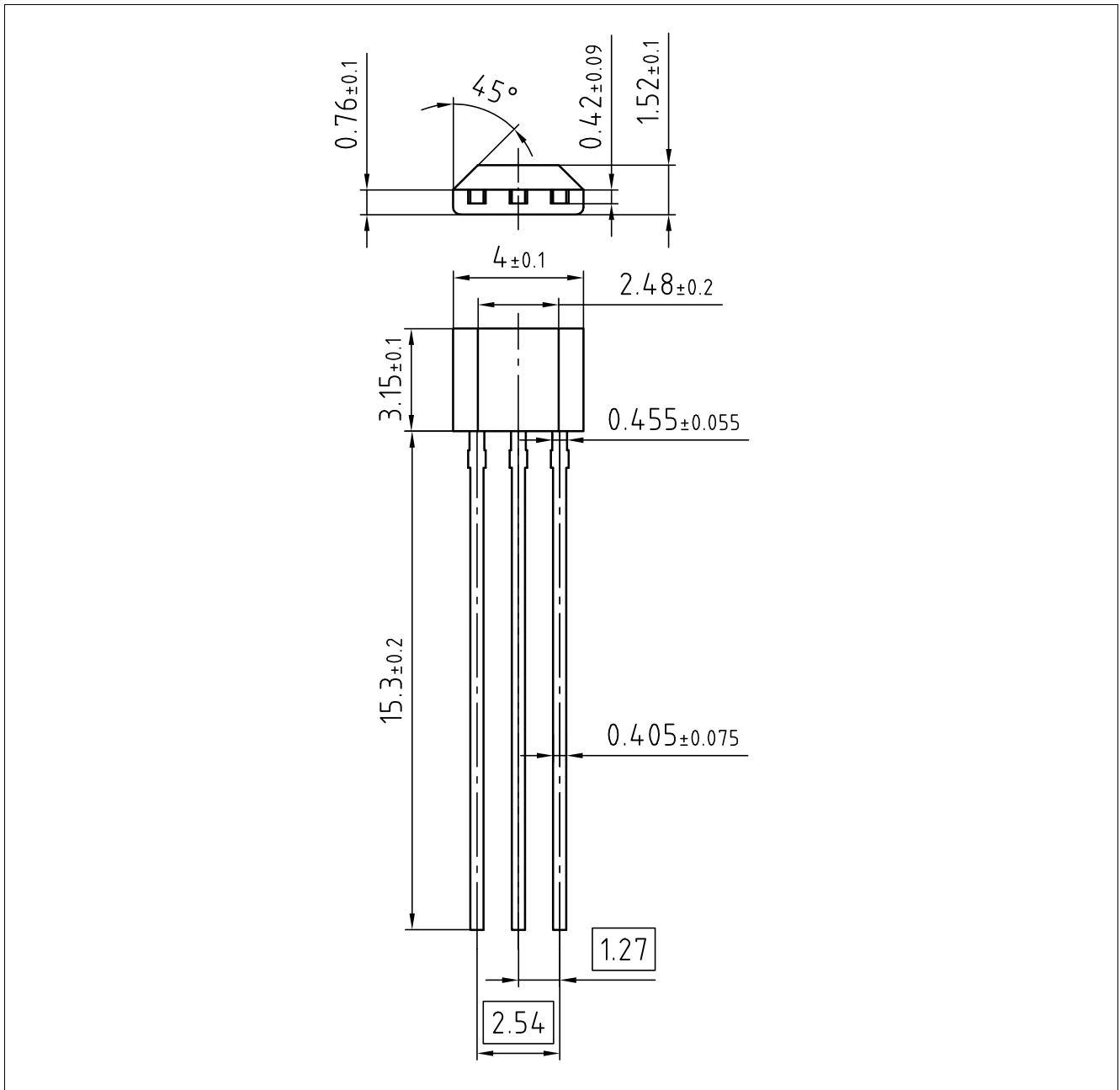


Figure 10 Package outline TLV4964-4TA: TO92S-3-1 (all dimensions in mm)

Package information

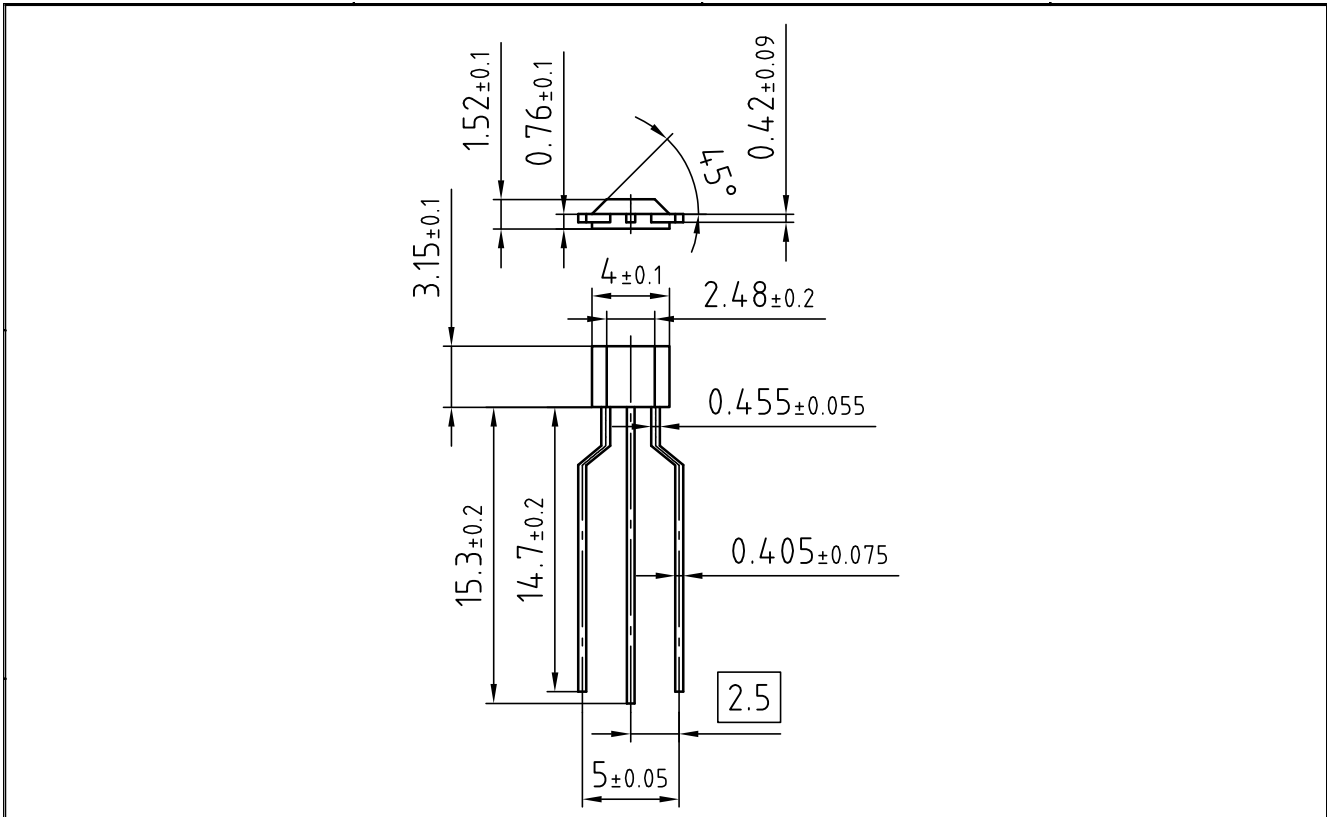


Figure 11 Package outline TLV4964-4TB; TO92S-3-2 (all dimensions in mm)

Package information

4.2 Packing information

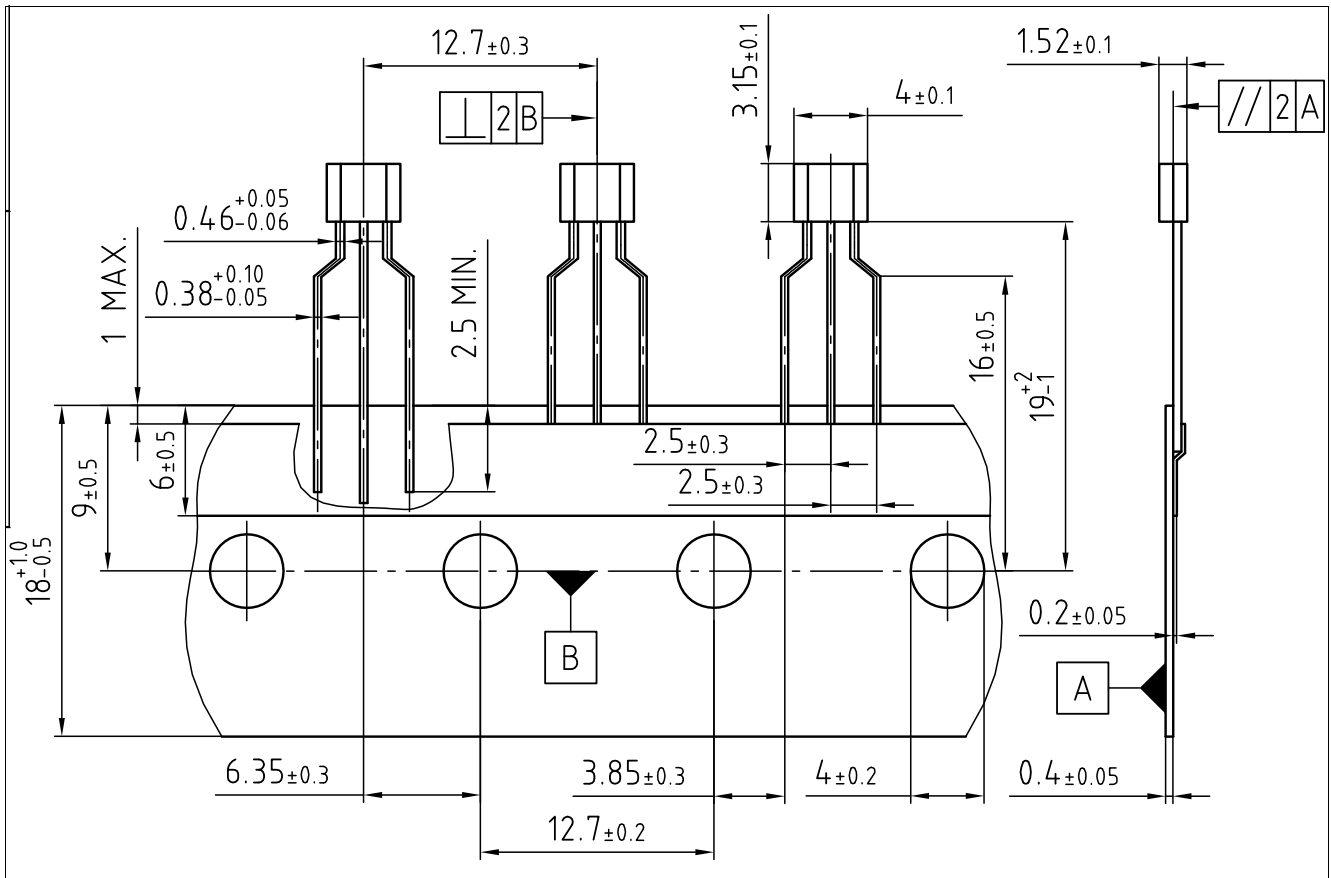


Figure 12 Packing information

4.3 Distance between chip and package

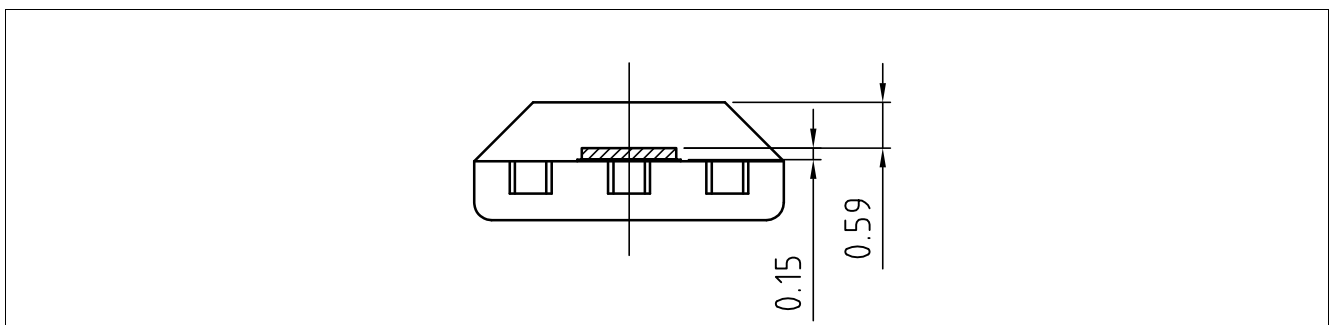


Figure 13 Distance between chip and package

Package information

4.4 Package marking

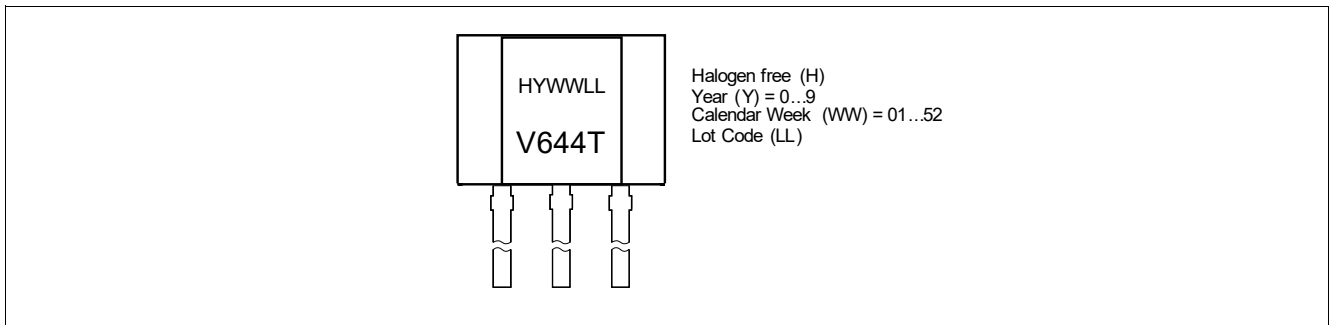


Figure 14 Marking of TLV4964-4T

Revision history**5 Revision history**

| Revision | Date | Changes |
|-----------------|-------------|--|
| Revision 1.2 | 2019-12-20 | Updated text and figure in Chapter 2.6 Updated standards in Table 4 Added maximum tested magnetic field in Chapter 3.3 Editorial changes |
| Revision 1.0 | 2015-05-18 | Initial release |

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